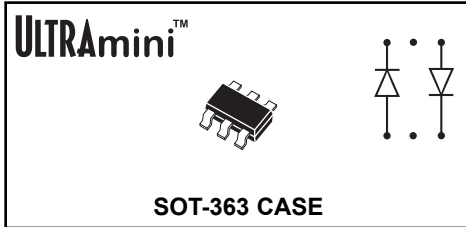


**CMKD6263DO**  
**SURFACE MOUNT**  
**ULTRAmi™**  
**DUAL OPPOSING**  
**HIGH VOLTAGE**  
**SILICON SCHOTTKY DIODES**



# Central™

**Semiconductor Corp.**

**FEATURES:**

- DUAL OPPOSING (DO) SCHOTTKY DIODES
- HIGH VOLTAGE (70V)
- LOW FORWARD VOLTAGE
- GALVANICALLY ISOLATED

**DESCRIPTION:**

The Central Semiconductor CMKD6263DO incorporates two galvanically isolated, High Voltage, low  $V_F$  Silicon Diodes with an opposing Anode/Cathode configuration, in a space saving SOT-363 surface mount package. These diodes are designed for fast switching applications requiring a low forward voltage drop.

**MARKING CODE: 63D**

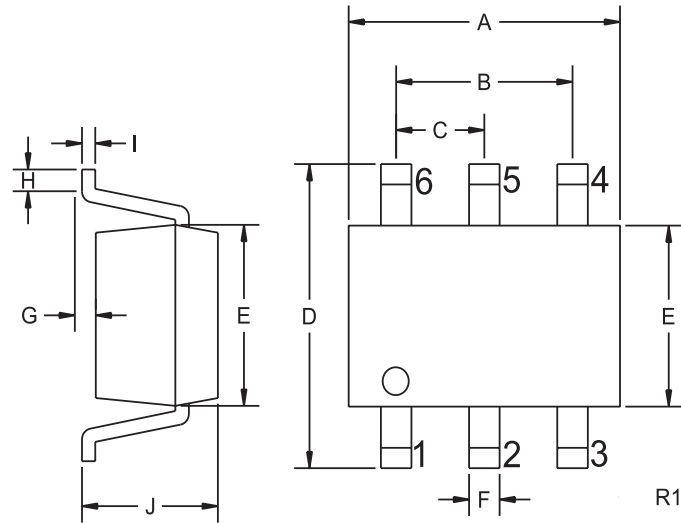
**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	70	V
Continuous Forward Current	$I_F$	15	mA
Forward Surge Current, $t_p=1.0$ s	$I_{FSM}$	50	mA
Power Dissipation	$P_D$	250	mW
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	500	$^\circ\text{C/W}$

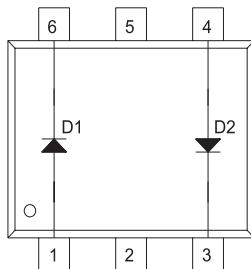
**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25^\circ\text{C}$ )

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=50\text{V}$		98	200	nA
$BV_R$	$I_R=10\mu\text{A}$	70			V
$V_F$	$I_F=1.0\text{mA}$		395	410	mV
$C_T$	$V_R=0\text{V}, f=1.0\text{MHz}$			2.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

SOT-363 CASE - MECHANICAL OUTLINE



Dual Opposing Configuration



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)

**LEAD CODE:**

- 1) ANODE D1
- 2) NC
- 3) CATHODE D2
- 4) ANODE D2
- 5) NC
- 6) CATHODE D1

**MARKING CODE: 63D**

R1 (13-November 2002)